

# OPA6428UR

Ultra Bright

## Ultra Red LED Chip

AlGaInP /GaAs

**1. Material** Substrate GaAs (N Type)  
Epitaxial Layer AlGaInP (P/N Type)

**2. Electrode** N (Cathode) Side Gold Alloy  
P (Anode) Side Gold Alloy

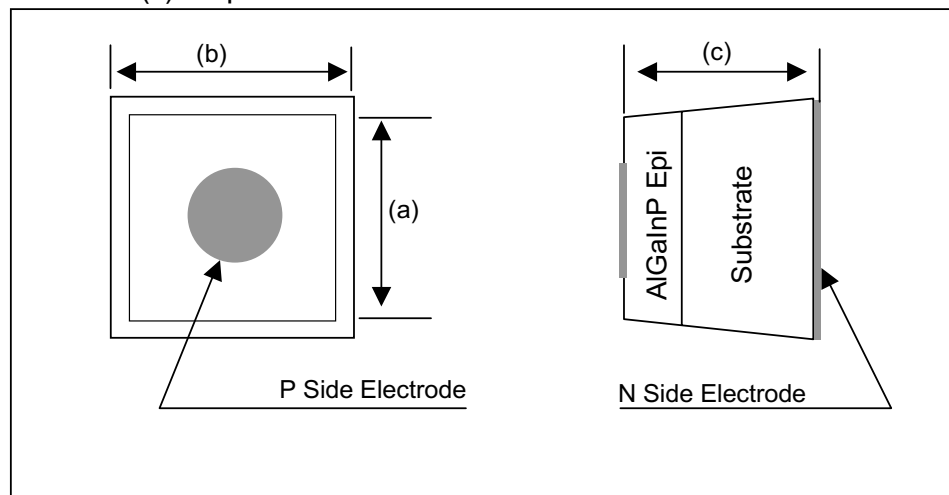
### 3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.7		V	$I_F=1mA$
	$V_{F(2)}$		2.0	2.3	V	$I_F=20mA$
Reverse Voltage	$V_R$	6.0			V	$I_R=100\mu A$
Brightness	$I_V$	A	14	20	mcd	$I_F=20mA$
		B	18	30		
		C	25	40		
		D	30	50		
		E	40	60		
		F	50	70		
Wavelength	$\lambda_P$		639		nm	$I_F=20mA$
	$\lambda_D$		631		nm	$I_F=20mA$
	$\Delta\lambda$		20		nm	$I_F=20mA$

※ Note : Assembled into TO-18 Header without resin coating.

### 4. Mechanical Data

- (a) Emission Area ----- 10mil × 10mil
- (b) Bottom Area ----- 11mil × 11mil
- (c) Chip Thickness ----- 7mil



Knowledge\*on Inc.

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